

PC3Q510NIP0F

*1-channel package type is also available. (model No. **PC3H510NIP0F**)

Mini-flat Half Pitch 4-channel Package Darlington Phototransistor Output, Low Input Current Photocoupler



■ Description

PC3Q510NIP0F contains a IRED optically coupled to a phototransistor.

It is packaged in a 4 channel Mini-flat package, Half pitch type.

Input-output isolation voltage(rms) is 2.5kV. CTR is MIN. 600% at input current of 0.5mA.

■ Features

- 1. 4-channel Mini-flat Half pitch package (Lead pitch : 1.27mm)
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. Low input current type (I_F=0.5mA)
- 4. Darlington phototransistor output (CTR : MIN. 600% at I_F =0.5mA, V_{CE} =2V)
- 5. Isolation voltage $(V_{iso(rms)}: 2.5kV)$
- 6. Lead-free and RoHS directive compliant

■ Agency approvals/Compliance

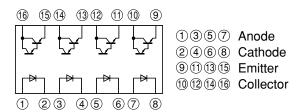
- Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. PC3Q51)
- 2. Package resin: UL flammability grade (94V-0)

■ Applications

- 1. Programmable controllers
- 2. Facsimiles
- 3. Telephones

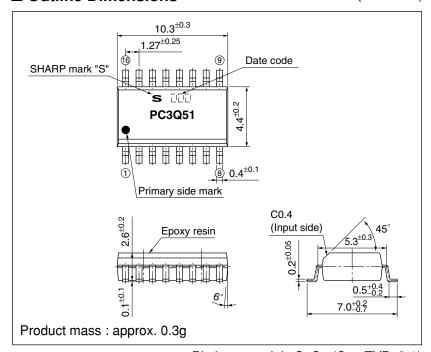


■ Internal Connection Diagram



■ Outline Dimensions

(Unit: mm)



Plating material : SnCu (Cu : TYP. 2%)



Date code (3 digit)

1st digit				2nd digit		3rd digit		
Year of production				Month of production		Week of production		
A.D.	Mark	A.D	Mark	Month	Mark	Week	Mark	
1990	A	2002	P	January	1	1st	1	
1991	В	2003	R	February	2	2nd	2	
1992	С	2004	S	March	3	3rd	3	
1993	D	2005	T	April	4	4th	4	
1994	Е	2006	U	May	5	5, 6th	5	
1995	F	2007	V	June	6			
1996	Н	2008	W	July	7			
1997	J	2009	X	August	8			
1998	K	2010	A	September	9			
1999	L	2011	В	October	0			
2000	M	2012	С	November	N			
2001	N	:	•	December	D			

repeats in a 20 year cycle

Country of origin Japan

Rank mark

There is no rank mark indicator.



■ Absolute Maximum Ratings

■ Absolute Maximum Ratings $(T_a=25^{\circ}C)$							
	Parameter	Symbol	Rating	Unit			
Input	Forward current	I_F	10	mA			
	*1 Peak forward current	I_{FM}	200	mA			
	Reverse voltage	V_R	6	V			
	Power dissipation	P	15	mW			
Output	Collector-emitter voltage	V_{CEO}	35	V			
	Emitter-collector voltage	V _{ECO}	6	V			
	Collector current	I_C	80	mA			
	Collector power dissipation	P_{C}	150	mW			
	Γotal power dissipation	P _{tot}	170	mW			
(Operating temperature	T_{opr}	-30 to +100	°C			
5	Storage temperature	T_{stg}	-40 to +125	°C			
*2]	Isolation voltage	V _{iso (rms)}	2.5	kV			
*3 (Soldering temperature	T_{sol}	260	°C			

^{*1} Pulse width≤100µs, Duty ratio : 0.001 *2 40 to 60%RH, AC for 1 minute, f=60Hz *3 For 10s

■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input	Forward voltage		V_{F}	I _F =5mA	-	1.2	1.4	V
	Reverse current		I_R	$V_R=4V$	_	_	10	μΑ
	Terminal capacitance		C_t	V=0, f=1kHz	_	30	250	pF
Output	Collector dark current		I_{CEO}	$V_{CE}=10V, I_{F}=0$	_	-	1000	nA
	Collector-emitter breakdown voltage		$\mathrm{BV}_{\mathrm{CEO}}$	$I_{C}=0.1 \text{ mA}, I_{F}=0$	35	_	_	V
	Emitter-collector breakdown voltage		BV_{ECO}	$I_E=10\mu A, I_F=0$	6	_	_	V
Transfer charac- teristics	Current transfer ratio		I_{C}	$I_F=0.5$ mA, $V_{CE}=2$ V	3	14	60	mA
	Collector-emitter saturation voltage		V _{CE (sat)}	$I_F=1mA$, $I_C=2mA$	_	_	1.0	V
	Isolation resistance		R_{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	_	Ω
	Floating capacitance		C_{f}	V=0, f=1MHz	-	0.6	1.0	pF
	Response time	Rise time	t _r	V 2V I 10 A D 1000	-	60	300	μs
		Fall time	t_{f}	$V_{CE}=2V$, $I_{C}=10mA$, $R_{L}=100\Omega$	_	53	250	μs



Fig.1 Forward Current vs. Ambient Temperature

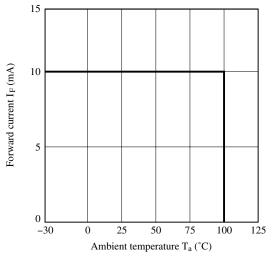


Fig.3 Collector Power Dissipation vs. Ambient Temperature

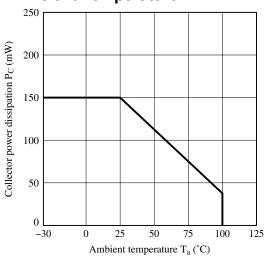


Fig.5 Peak Forward Current vs. Duty Ratio

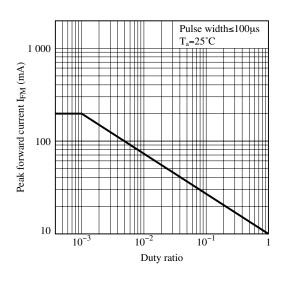


Fig.2 Diode Power Dissipation vs. Ambient Temperature

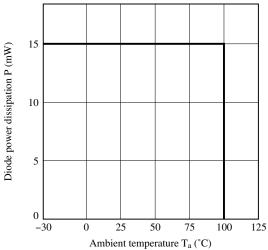


Fig.4 Total Power Dissipation vs. Ambient Temperature

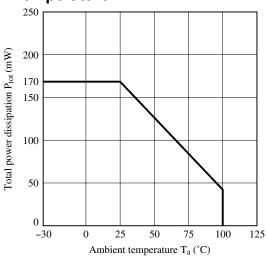


Fig.6 Forward Current vs. Forward Voltage

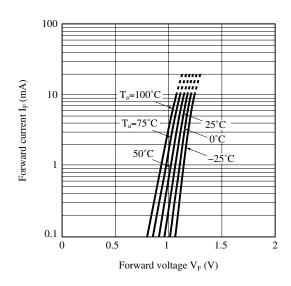




Fig.7 Current Transfer Ratio vs. Forward Current

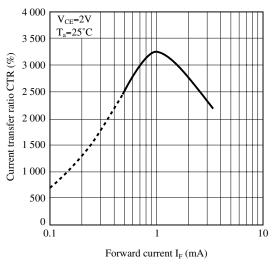


Fig.9 Collector Current vs. Collector-emitter Voltage

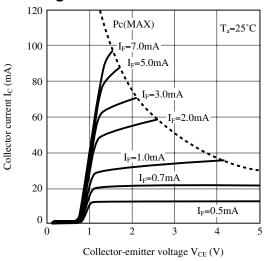


Fig.11 Collector - emitter Saturation Voltage vs. Ambient Temperature

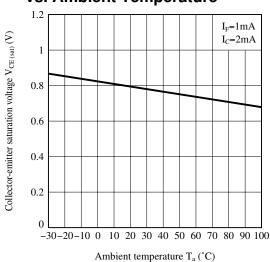


Fig.8 Collector Current vs. Forward Current

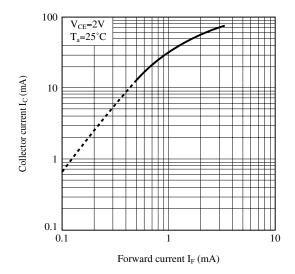


Fig.10 Relative Current Transfer Ratio vs.
Ambient Temperature

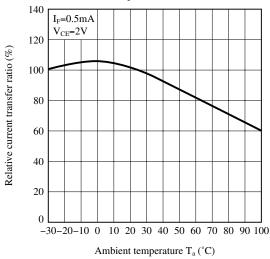
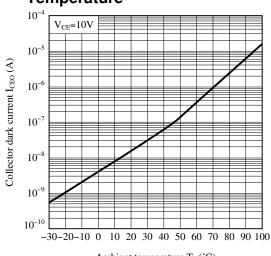


Fig.12 Collector Dark Current vs. Ambient Temperature

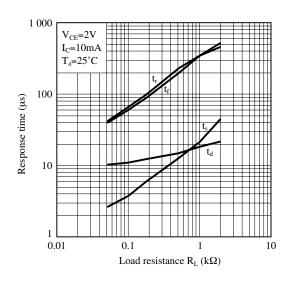


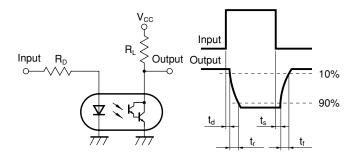
Ambient temperature T_a (°C)



Fig.13 Response Time vs. Load Resistance

Fig.14 Test Circuit for Response Time





Please refer to the conditions in Fig.13

Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.



■ Design Considerations

Design guide

While operating at I_F<0.5mA, CTR variation may increase.

Please make design considering this fact.

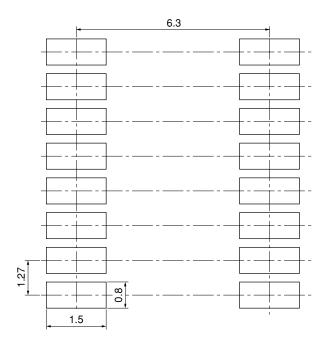
This product is not designed against irradiation and incorporates non-coherent IRED.

Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

Recommended Foot Print (reference)



(Unit: mm)

[☆] For additional design assistance, please review our corresponding Optoelectronic Application Notes.



■ Manufacturing Guidelines

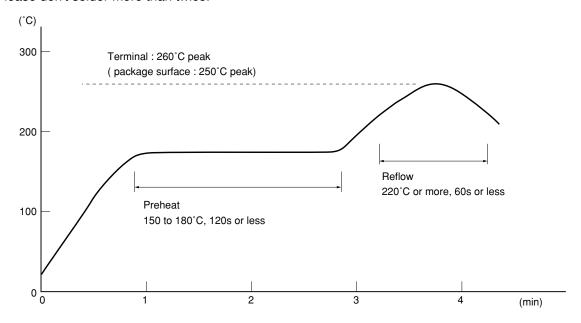
Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please don't solder more than twice.



Flow Soldering:

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 260°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C.

Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3 minutes or less

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).

Sheet No.: D2-A02402EN



■ Package specification

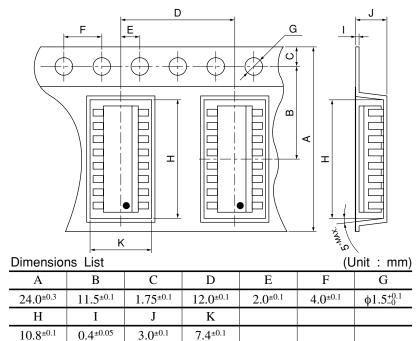
● Tape and Reel package

Package materials Carrier tape : PS

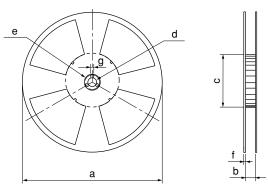
Cover tape: PET (three layer system)

Reel: PS

Carrier tape structure and Dimensions

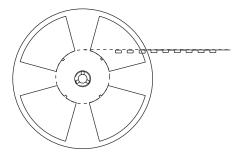


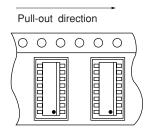
Reel structure and Dimensions



Dimens	ions List	(Unit: mm)		
a	b	c	d	
330	25.5±1.5	100±1.0	13±0.5	
e	f	g		
23±1.0	2.0 ^{±0.5}	2.0±0.5		

Direction of product insertion





[Packing: 1 000pcs/reel]



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[E204] Sheet No.: D2-A02402EN